

LMC6008 **8 Channel Buffer**

General Description

The LMC6008 octal buffer is designed specifically to buffer the multi-level voltages going to the inputs of the integrated circuits. The LMC6008 AC characteristics, including settling time, are specified for a capacitive load of 0.1 μF for this reason.

The LMC6008 contains 4 high-speed buffers and 4 lowpower buffers. The high-speed buffers can provide an output current of at least 250 mA (minimum), and the low-power buffers can provide at least 150 mA (minimum). By including the 2 types of buffers, the LMC6008 is able to provide this function while consuming a supply current of only 6.5 mA (maximum). The buffers are a rail-to-rail design, which typically swing to within 30 mV of either supply.

The LMC6008 also contains a standby function which puts the buffer into a high-impedance mode. The supply current in the standby mode is a low 500 μA max. Also, a thermal limit circuit is included to protect the device from overload conditions.

Features

High Output Current:	
High Speed Buffers	250 mA min
Low Power Buffers	150 mA min
Slew Rate:	
High Speed Buffers	1.7 V/μs
Low Power Buffers	0.85V/µs
Settling Time, $C_L = 0.1 \ \mu F$	16 μs max
Wide Input/Output Range	0.1V to V _{CC} $-$ 0.1V min
 Supply Voltage Range 	5V to 16V
 Supply Current 	6.5 mA max
 Standby Mode Current 	500 μA

Applications

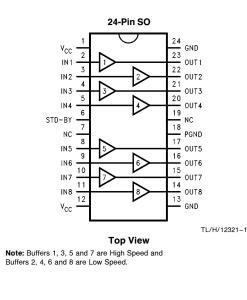
- AMLCD voltage buffering
- Multi-voltage buffering

Ordering Information

Package	Temperature Range - 40°C to + 85°C	NSC Drawing	Transport Media
	LMC6008IM	M24B	Rail
Surface Mount	LMC6008IMX	M24B	Tape & Reel

Connection Diagram

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TL/H/12321

RRD-B30M56/Printed in U. S. A.

LMC6008

April 1996

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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications. ESD Tolerance (Note 2) 2000V

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ESD Tolerance (Note 2)	2000V
Voltage at Input Pin	V^+ + 0.4V, V^- - 0.4V
Voltage at Output Pin	V^+ + 0.4V, V^- - 0.4V
Supply Voltage (V $^+$ – V $^-$)	16V
Lead Temperature	

Operating Ratings (Note 1)

Supply Voltage	$4.5V \leq V^+ \leq 16V$
Temperature Range	-20° C to $+100^{\circ}$ C
Thermal Resistance (θ _{JA}) Μ Package, 24-Pin Surface Mount	50°C/W

DC Electrical Characteristics

(soldering, 10 sec.)

Storage Temperature Range

Power Dissipation (Note 4)

Junction Temperature (Note 4)

Unless otherwise specified, all limits guaranteed for T_J = 25°C, V_{CC} = 14.5V and R_L = 0.

260°C

150°C

-55°C to +150°C

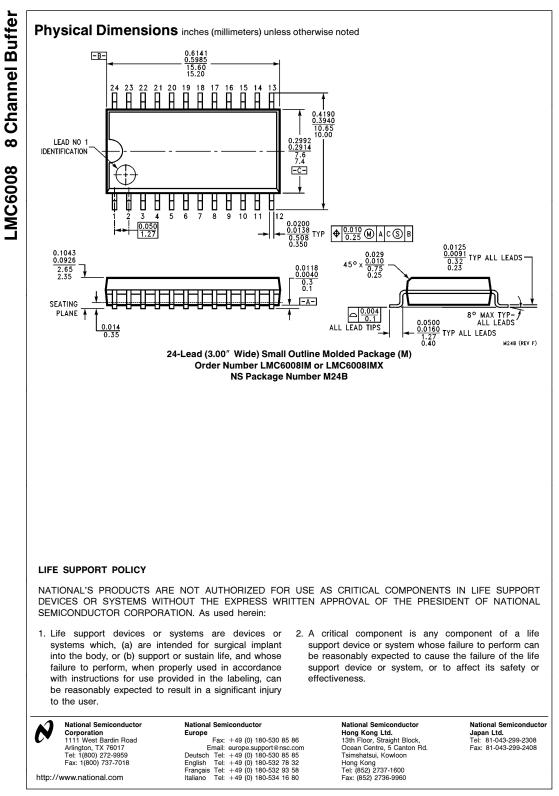
Internally Limited

Symbol	Parameter	Conditions	Typ (Note 5)	LMC6008 Limit (Note 6)	Units
V _{OS}	Input Offset Voltage	$R_{S} = 10 k\Omega$		25	mV max
A _V	$V_{O} = 10 V_{PP}$			0.985	V/V
I _B	Input Bias Current			300	nA max
I _{LP}	Peak Load Current	Hi Speed Buffers		-250	mA max
		V _O = 13 V _{PP}		+ 250	mA min
I _{LP}	Peak Load Current	Lo Speed Buffers		-150	mA max
		V _O = 13 V _{PP}		+ 150	mA min
V _{ERR}	Output Voltage Difference (Note 9)		35		mV max
V _{IH}	Standby Logic HIgh Voltage			3.30	V min
V _{IL}	I _{STANDBY} Logic Low Voltage			1.80	V max
I _{IH}	Standby High Input Current			1.0	μA max
۱ _{IL}	Standby Low Input Current			1.0	μA max
IO (STD-BY)	Output Leakage Current	$V_{STD-BY} = High$		5	μA max
ICC	Supply Current	$V_{IL} = Low, V_{IN} = 7.25V$		6.5	mA max
I _{STD-BY}	Standby Current	V _{STD-BY} = High		500	μA max
PSRR	Power Supply Rejection Ratio	$5V < V_{CC} < 14.5V$		55	dB min
Vo	Voltage Output Swing			0.1	V min
				V _{CC} - 0.1	V max

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